

Product Summary

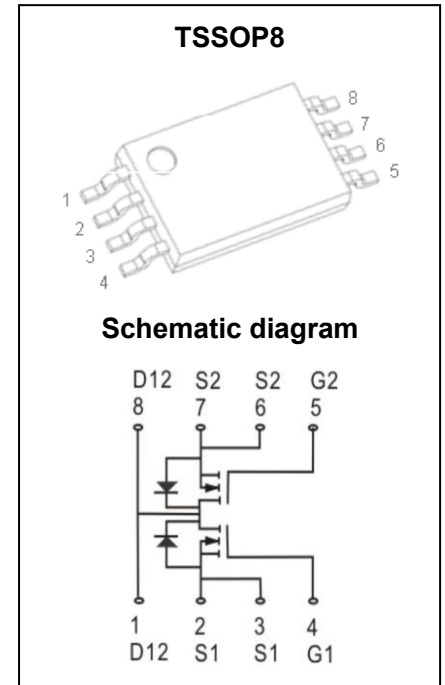
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	26mΩ@4.5V	4A
	32mΩ@2.5V	

Feature

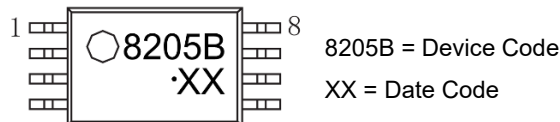
- TrenchFET Power MOSFET
- Excellent $R_{DS(on)}$
- Low Gate Charge
- High Power and Current Handling Capability
- Surface Mount Package

Application

- Battery Protection
- Load Switch
- Power Management



MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^{1,2}	I_D	4	A
Pulsed Drain Current	I_{DM}	16	A
Power Dissipation	P_D	2	W
Thermal Resistance from Junction to Ambient ^{1,2}	$R_{\theta JA}$	62.5	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~ +150	$^\circ\text{C}$

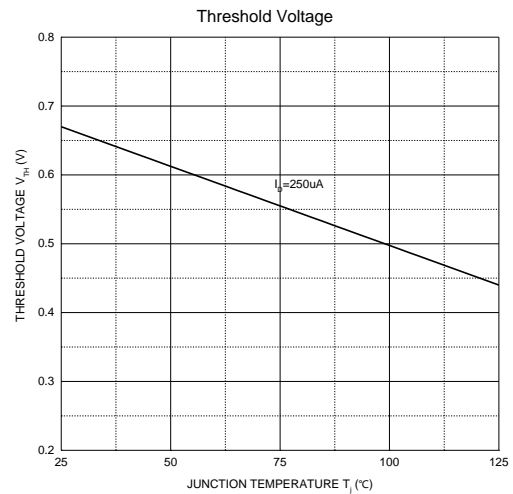
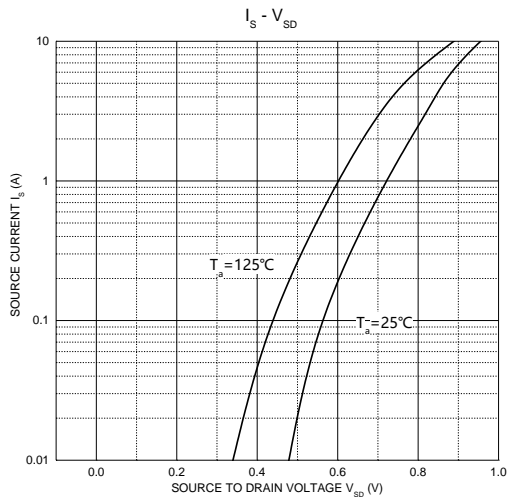
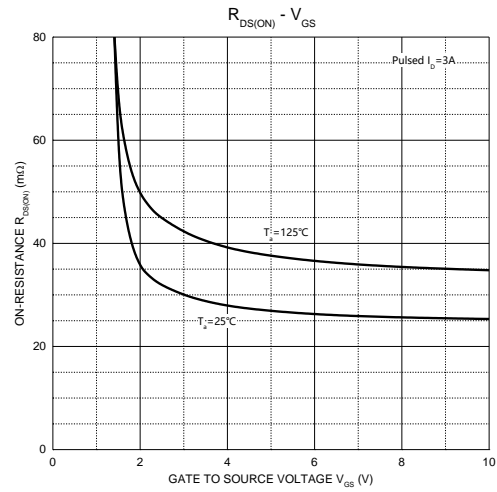
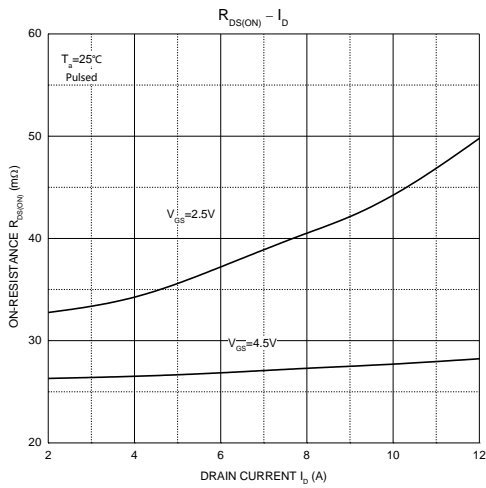
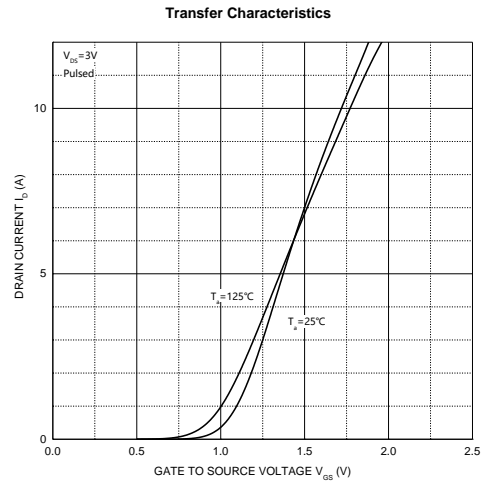
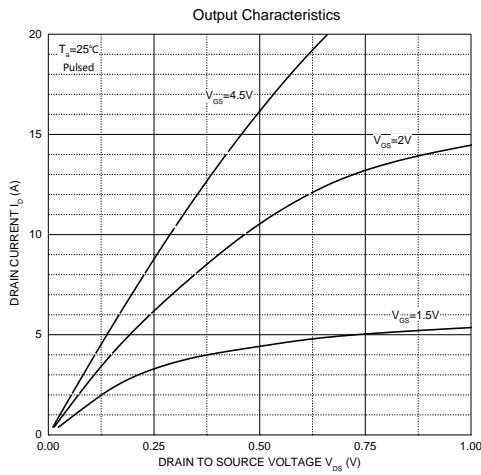
MOSFET ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0V$			± 100	nA
On Characteristics³						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.45	0.7	1.2	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3A$		26	32	m Ω
		$V_{GS} = 2.5V, I_D = 3A$		32	40	
Forward Transconductance	g_{fs}	$V_{DS} = 5V, I_D = 3A$		8		S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1MHz$		278		pF
Output Capacitance	C_{oss}			51		
Reverse Transfer Capacitance	C_{rss}			44		
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 10V, V_{GS} = 4.5V, I_D = 4A$		14		nC
Gate-Source Charge	Q_{gs}			2.5		
Gate-Drain Charge	Q_{gd}			2.5		
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 10V, V_{GS} = 4V, I_D = 1A, R_G = 10\Omega$		16		ns
Turn-on rise time	t_r			8		
Turn-off delay time	$t_{d(off)}$			36		
Turn-off fall time	t_f			18		
Diode Characteristics						
Diode Forward Current	I_S				4	A
Diode Forward Voltage ³	V_{SD}	$V_{GS} = 0V, I_S = 3A$			1.2	V

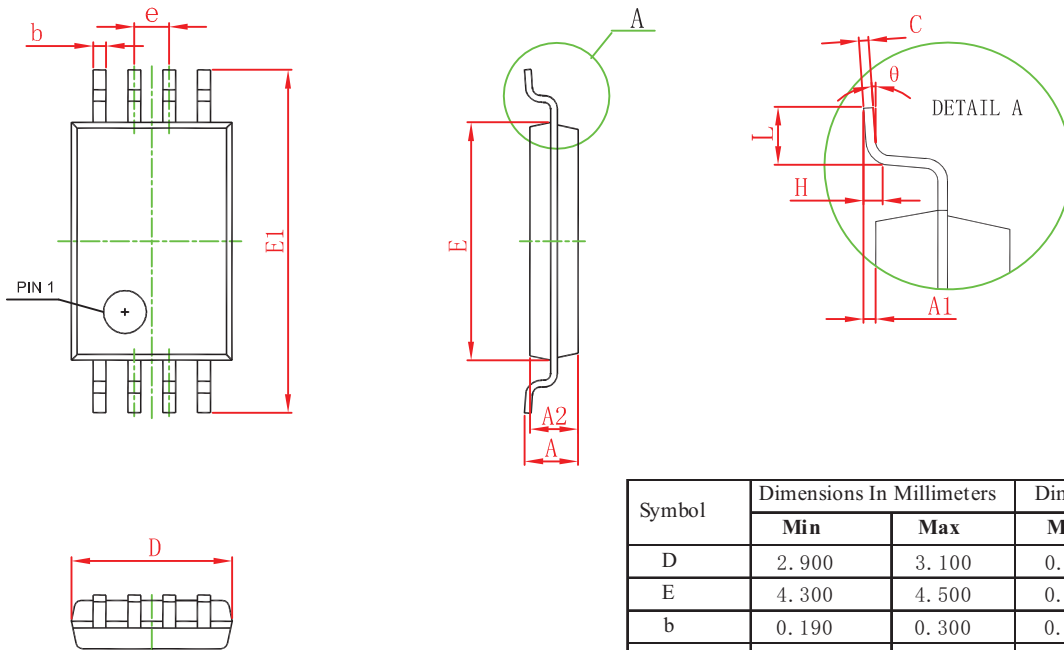
Notes:

- $R_{\theta JA}$ is measured with the device mounted on 1 in² FR4 board with 1 oz. single side copper, in a still air environment with $T_a = 25^\circ\text{C}$.
- $R_{\theta JA}$ is measured in the steady state
- Pulse test : Pulse width $\leq 380\mu s$, duty cycle $\leq 2\%$.

Typical Electrical and Thermal Characteristics



TSSOP8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
c	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25(TYP)		0.01(TYP)	
θ	1°	7°	1°	7°

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)